430V N-Channel MOSFET

Lead Free Package and Finish

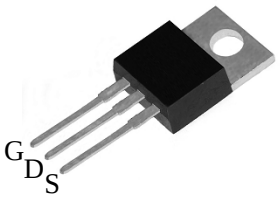
BV_{DSS}	$R_{DS(ON),typ.}$	I_D
430V	0.39Ω	11A

General Features

- Proprietary New Planar Technology
- $R_{DS(ON),typ.}$=0.39 Ω@V_{GS}=10V
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

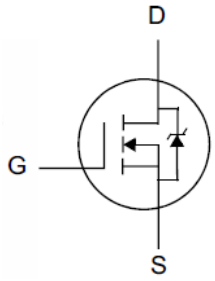
Applications

- Ballast and Lighting
- DC-AC Inverter
- Other Applications



TO-220

Package No to Scale



Ordering Information

Part Number	Package	Brand
PTP11N45	TO-220	

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	PTP11N45	Unit
V_{DSS}	Drain-to-Source Voltage[1]	430	V
V_{GSS}	Gate-to-Source Voltage	±30	
I_D	Continuous Drain Current	11	A
$I_{D\ @\ Tc=100℃}$	Continuous Drain Current @ Tc=100℃	Figure 3	
I_{DM}	Pulsed Drain Current at V_{GS}=10V[2]	Figure 6	
E_{AS}	Single Pulse Avalanche Energy	500	mJ
dv/dt	Peak Diode Recovery dv/dt[3]	5.0	V/ns
P_D	Power Dissipation	140	W
	Derating Factor above 25℃	1.12	W/℃
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	℃
T_J& T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	PTP11N45	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.89	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	

Electrical Characteristics

OFF Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	430	--	--	V	V_{GS}=0V, I_D=250uA
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	uA	V_{DS}=430V, V_{GS}=0V
		--	--	100		V_{DS}=360V, V_{GS}=0V, T_J =125℃
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	V_{GS}=+30V, V_{DS}=0V
		--	--	-100		V_{GS}=-30V, V_{DS}=0V

ON Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance[4]	--	0.39	0.50	Ω	V_{GS}=10V, I_D=5.5A
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=V_{GS}, I_D=250uA
gfs	Forward Transconductance[4]	--	12	--	S	VDS=20V,ID=10A

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	1250	--	pF	V_{GS}=0V, V_{DS}=25V, f=1.0MH_Z
C_{rss}	Reverse Transfer Capacitance	--	20	--		
C_{oss}	Output Capacitance	--	150	--		
Q_g	Total Gate Charge	--	28	--	nC	V_{DD}=200V, I_D=11A, V_{GS}=0 to 10V
Q_{gs}	Gate-to-Source Charge	--	7.0	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	11	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	14	--	nS	V_{DD}=200V, I_D =11A, V_{GS}= 10V R_G=12Ω
t_{rise}	Rise Time	--	25	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	44	--		
t_{fall}	Fall Time	--	28	--		

Source-Drain Body Diode Characteristics

T_J=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current[4]	--	--	11	A	Integral PN-diode in MOSFET
I_{SM}	Pulsed Source Current[4]	--	--	40		
V_{SD}	Diode Forward Voltage	--	--	1.5	V	I_S=10A, V_{GS}=0V
trr	Reverse recovery time	--	303	--	ns	V_{GS}=0V ,I_F=10, di_F/dt=100A/μs
Qrr	Reverse recovery charge	--	1.8	--	uC	

Note:

[1] T_J=+25℃ to +150℃
[2] Repetitive rating; pulse width limited by maximum junction temperature.
[3] I_{SD}= 10A di/dt < 100 A/μs, V_{DD} < BV_{DSS}, T_J=+150℃.
[4] Pulse width≤380μs; duty cycle≤2%.

Typical Characteristics

Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

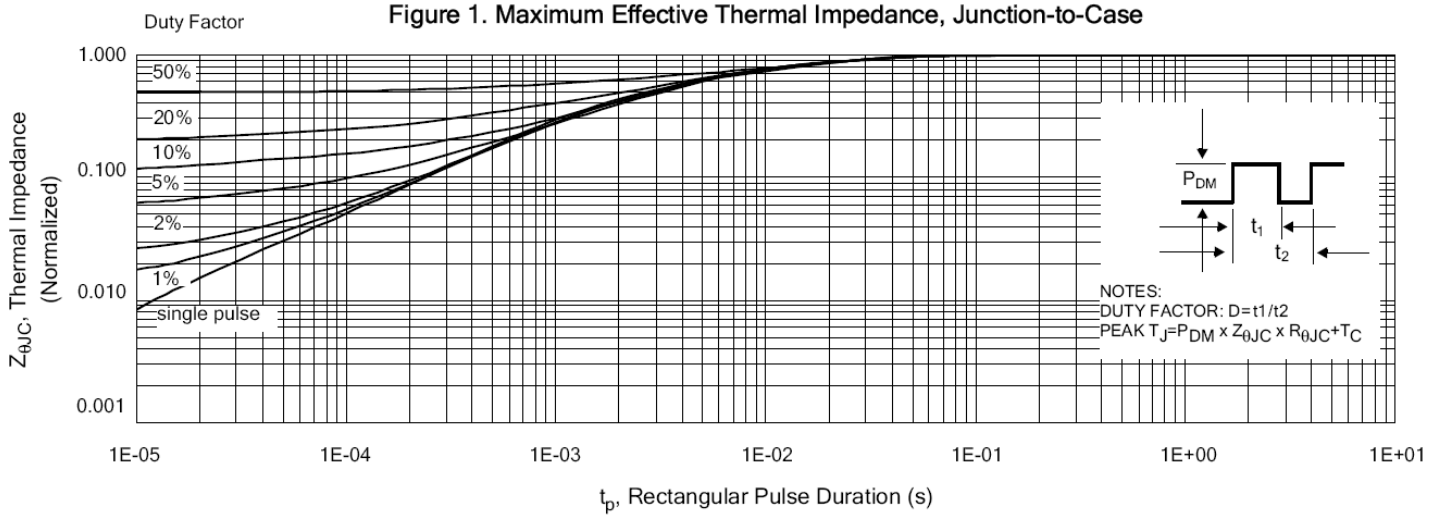


Figure 2. Maximum Power Dissipation vs Case Temperature

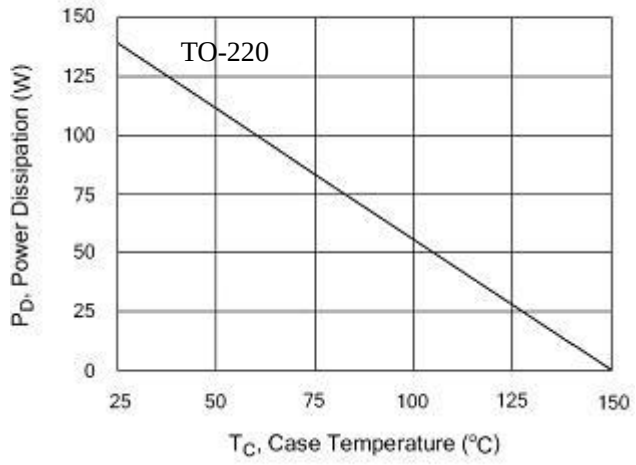


Figure 3 .Maximum Continuous Drain Current vs Tc

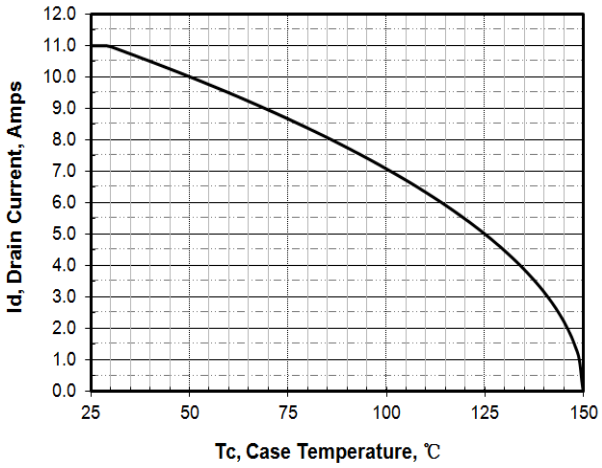


Figure 4. Typical Output Characteristics

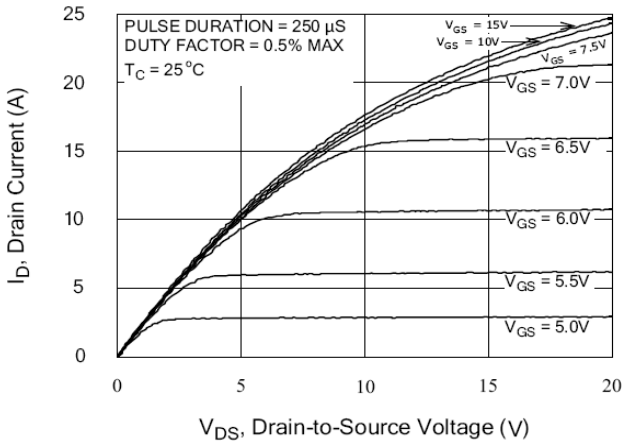
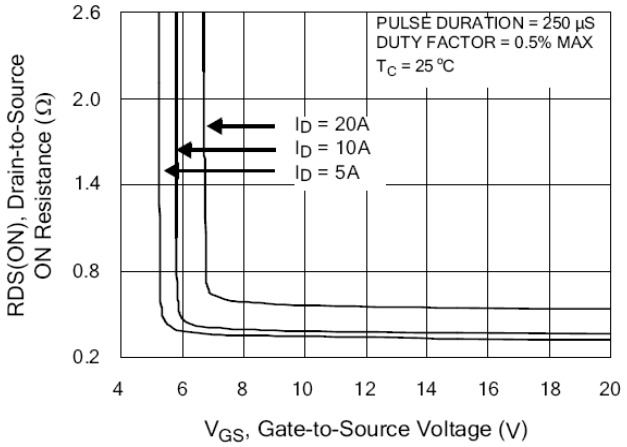


Figure5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current



Typical Characteristics(Cont.)

Figure 6. Peak Current Capability

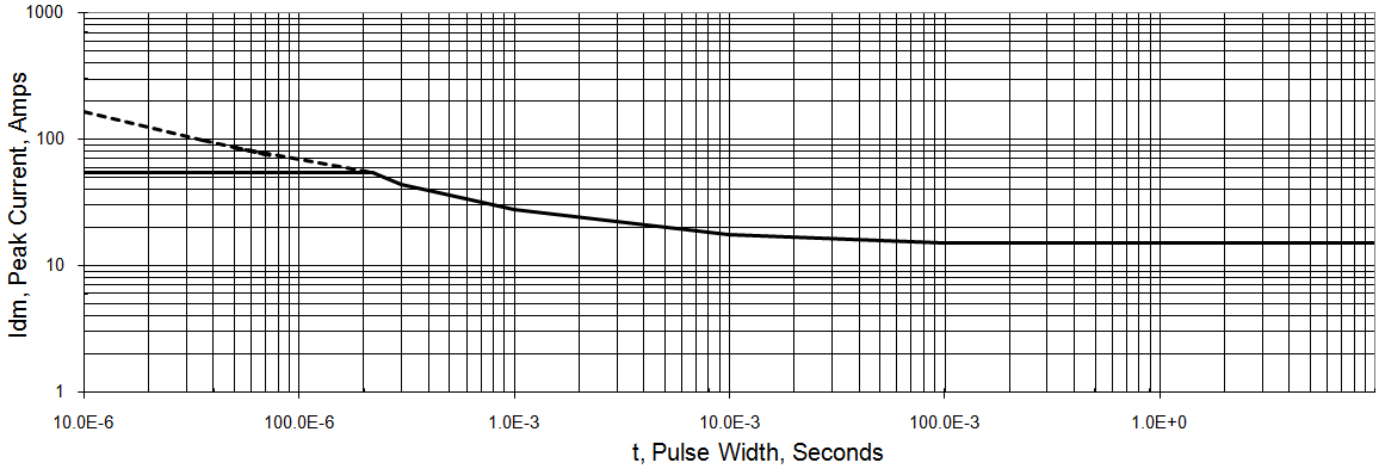


Figure 7. Typical Transfer Characteristics

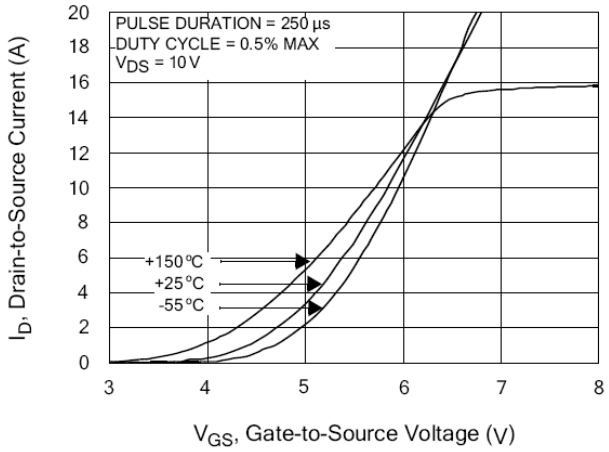


Figure8. Unclamped Inductive Switching Capability

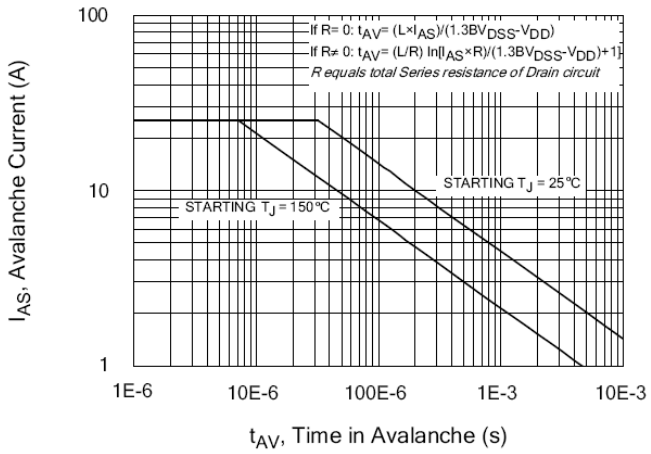


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

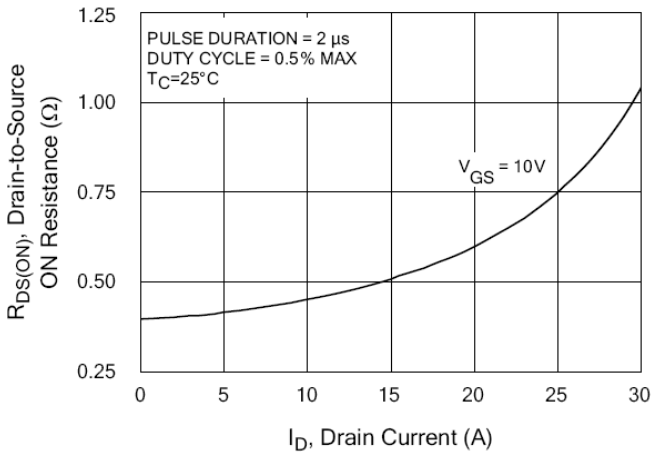
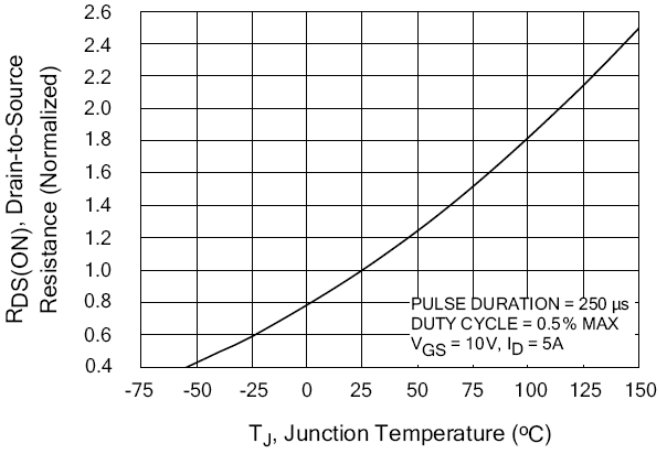


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature



Typical Characteristics(Cont.)

Figure 11. Typical Breakdown Voltage vs Junction Temperature

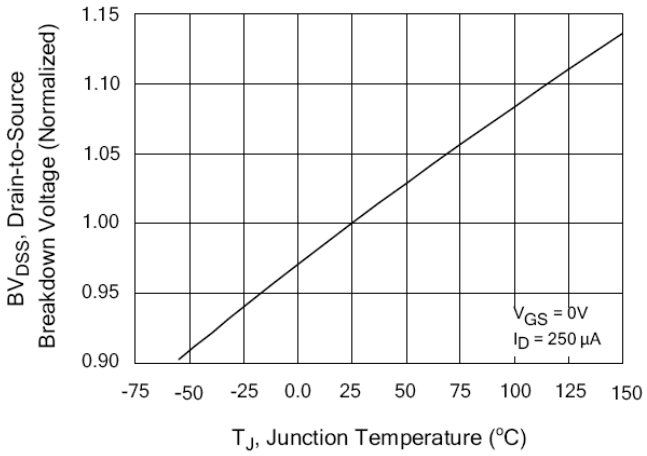


Figure 12. Typical Threshold Voltage vs Junction Temperature

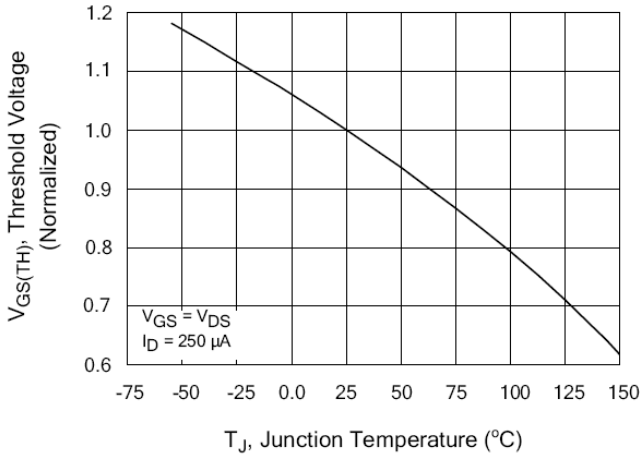


Figure 13 . Maximum Safe Operating Area

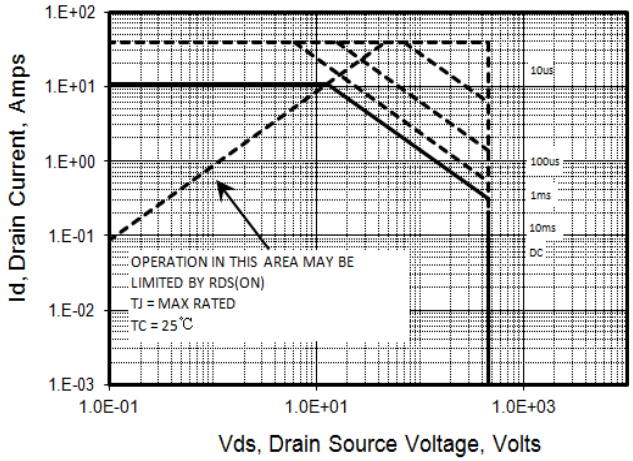


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

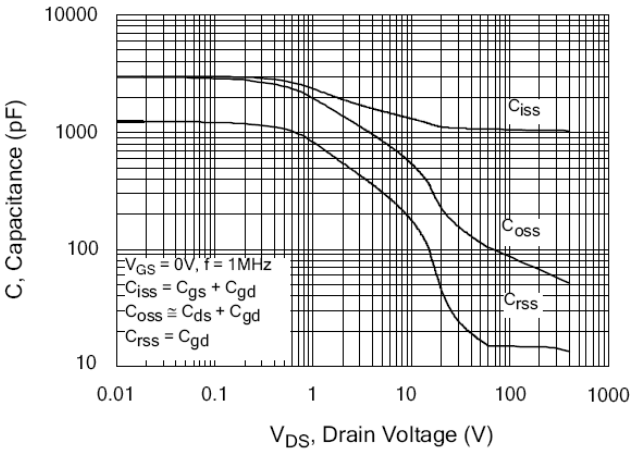


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

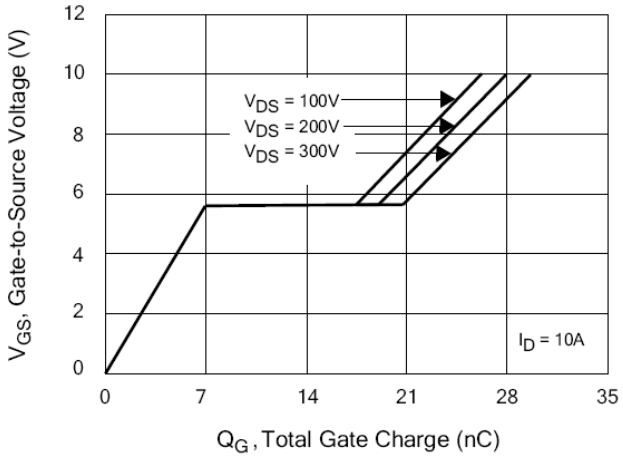
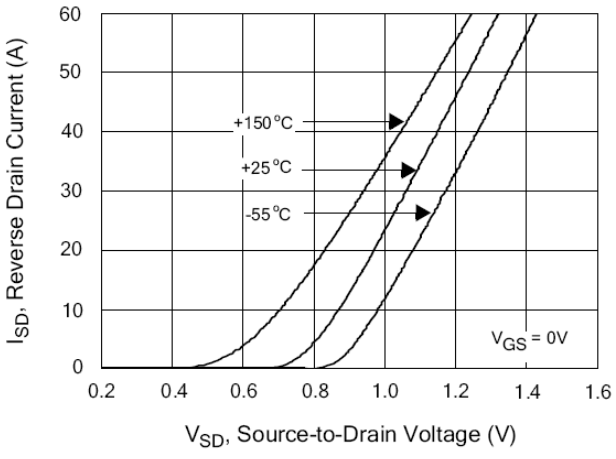


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuits and Waveforms

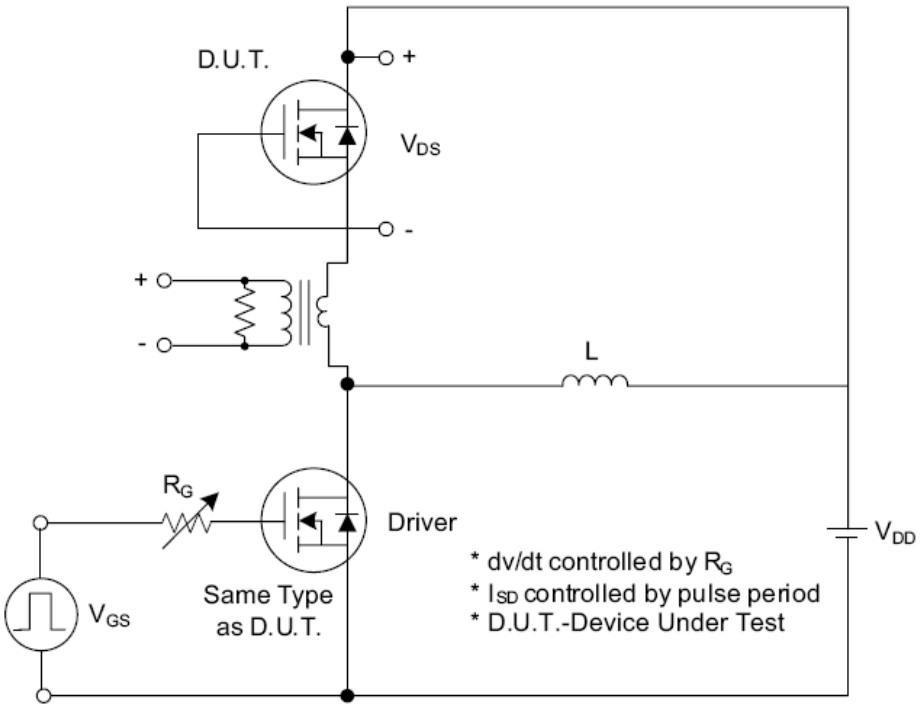


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

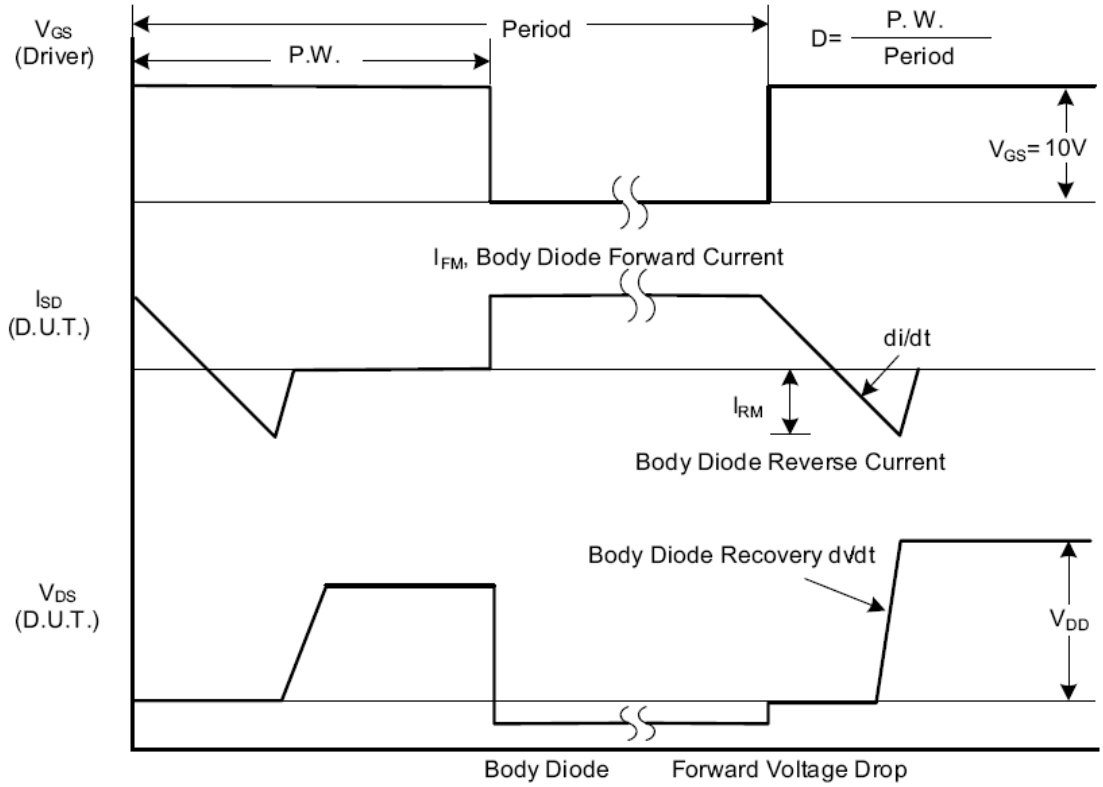


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

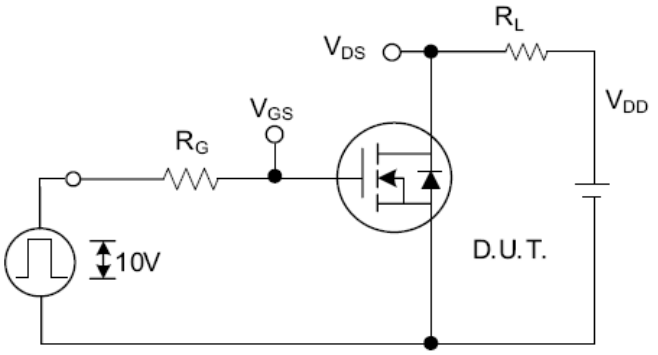


Fig. 2.1 Switching Test Circuit

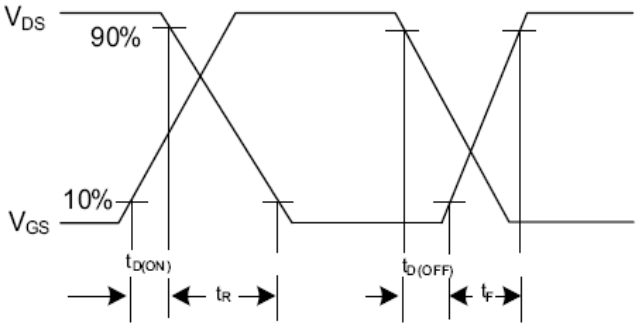


Fig. 2.2 Switching Waveforms

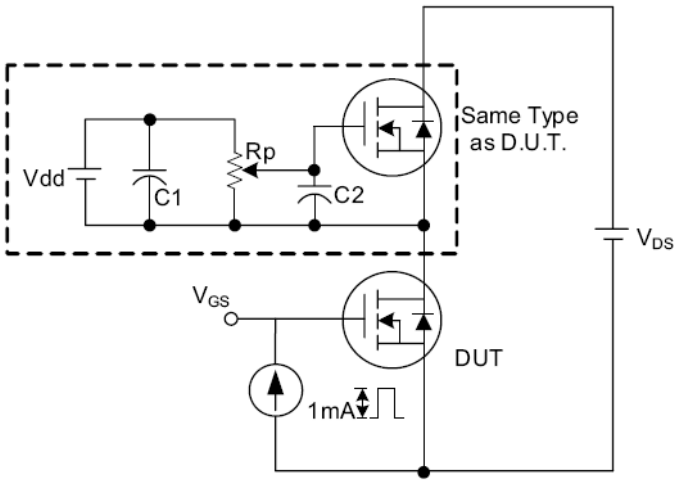


Fig. 3 . 1 Gate Charge Test Circuit

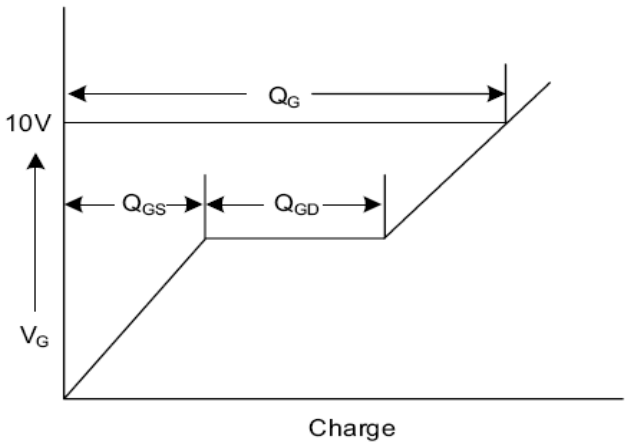


Fig. 3 . 2 Gate Charge Waveform

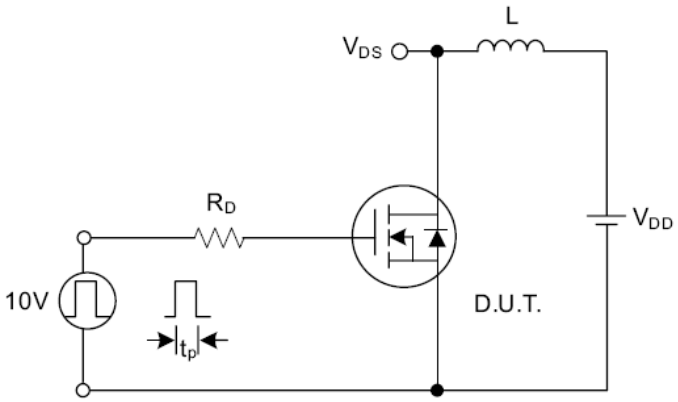


Fig. 4.1 Unclamped Inductive Switching Test Circuit

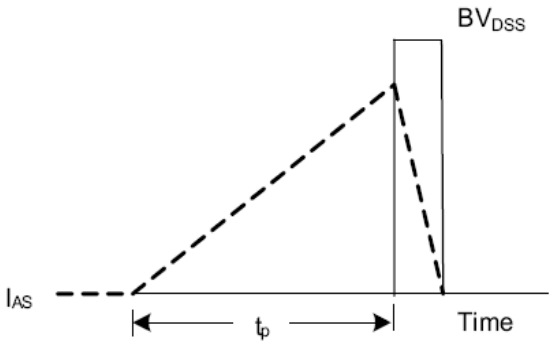


Fig. 4.2 Unclamped Inductive Switching Waveforms

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